

SOT-23


- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

MARKING: G1
Features

- Complementary to MMBT5401
- Epitaxial planar die construction
- Power Dissipation of 300mW

Maximum Ratings

(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter -Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	I _c	600	mA
Collector Power Dissipation	P _c	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	416	°C/W

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =100μA, I _E =0	180		V
Collector-emitter breakdown voltage	V(BR)CEO *	I _C =1mA, I _B =0	160		V
Emitter-base breakdown voltage	V(BR)EBO	I _E =10μA, I _C =0	6		V
Collector cut-off current	I _{CBO}	V _{CB} =120V, I _E =0		50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0		50	nA
DC current gain	hFE(1) *	V _{CE} =5V, I _C =1mA	80		
	hFE(2) *	V _{CE} =5V, I _C =10mA	100	300	
	hFE(3) *	V _{CE} =5V, I _C =50mA	30		
Collector-emitter saturation voltage	VCE(sat)1 *	I _C =10mA, I _B =1mA		0.15	V
	VCE(sat)2 *	I _C =50mA, I _B =5mA		0.20	V
Base -emitter saturation voltage	VBE(sat)1 *	I _C =10mA, I _B =1mA		1.00	V
	VBE(sat)2 *	I _C =50mA, I _B =5mA		1.00	V
Transition frequency	f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100	300	MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		6	pF

*Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2.0%

CLASSIFICATION OF hFE(2)

HFE	100-300	
RANK	L	H
RANGE	100-200	200-300

